

**Amendments to the Claims:**

This listing of the claims will replace all prior versions and listings of the claims in the application:

**Listing of Claims:**

1. (Canceled).
2. (Currently Amended) An integrated circuit electrode according to Claim [[1]] 14 wherein the second metal also has higher oxygen affinity than the first metal..
3. (Currently Amended) An integrated circuit electrode ~~according to Claim 4~~ comprising:  
an alloy comprising a first metal and a second metal having lower work function than the first metal, wherein the first metal is selected from the group consisting of Co, Ni, Pd, Rh, Ru, Ir, Pt, Au, Re, Os, RuO<sub>2</sub>, IrO<sub>2</sub> and alloys thereof and wherein the second metal is selected from the group consisting of Mn, Mg, V, Ti, Cr, Y, Zr, Ta, La, Gd, Sm, Pr, Nb, Al, Hf and alloys thereof.
4. (Currently Amended) An integrated circuit electrode according to Claim [[1]] 14 wherein the first metal is Ru and the second metal is Ta.
5. (Canceled).
6. (Canceled).
7. (Canceled).
8. (Canceled).
9. (Currently Amended) An integrated circuit ~~electrode according to Claim 6~~ comprising:

first spaced apart source and drain regions in an integrated circuit substrate;  
a first gate insulating region on the integrated circuit substrate between the  
first spaced apart source and drain regions;

a first gate electrode on the first gate insulating region opposite the integrated  
circuit substrate, wherein the first gate electrode comprises an alloy comprising Ru  
and Ta;

second spaced apart source and drain regions in the integrated circuit substrate  
and of opposite conductivity type than the first spaced apart source and drain regions;

a second gate insulating region on the integrated circuit substrate between the  
second spaced apart source and drain regions; and

a second gate electrode on the second gate insulating region opposite the  
integrated circuit substrate, wherein the second gate electrode comprises an alloy  
comprising the first metal and the second metal Ru and Ta and having different  
amounts of the first metal Ru relative to the second metal Ta than the first gate  
electrode.

10. (Currently Amended) An integrated circuit ~~electrode~~ according to Claim ~~[[7]]~~ 9 wherein the first spaced apart source and drain regions are n-type spaced apart source and drain regions and wherein the second spaced apart source and drain regions are p-type spaced apart source and drain regions.

11. (Currently Amended) An integrated circuit ~~electrode~~ according to Claim 9 wherein the first spaced apart source and drain regions are n-type spaced apart source and drain regions, wherein the second spaced apart source and drain regions are p-type spaced apart source and drain regions and wherein the second gate electrode comprises a higher percentage of ~~the first metal~~ Ru relative to ~~the second~~ Ta than the first gate electrode.

12. (Currently Amended) An integrated circuit ~~electrode according to~~  
~~Claim 11~~ comprising:

n-type spaced apart source and drain regions in an integrated circuit substrate;

a first gate insulating region on the integrated circuit substrate between the n-type spaced apart source and drain regions;

a first gate electrode on the first gate insulating region opposite the integrated circuit substrate;

p-type spaced apart source and drain regions in the integrated circuit substrate;

a second gate insulating region on the integrated circuit substrate between the p-type spaced apart source and drain regions; and

a second gate electrode on the second gate insulating region opposite the integrated circuit substrate,

wherein the first gate electrode comprises an Ru-Ta alloy having between about 40% Ta and about 54% Ta and wherein the second gate electrode comprises an Ru-Ta alloy having less than about 20% Ta.

13. (Currently Amended) An integrated circuit ~~electrode according to Claim 11~~ comprising:

n-type spaced apart source and drain regions in an integrated circuit substrate;

a first gate insulating region on the integrated circuit substrate between the n-type spaced apart source and drain regions;

a first gate electrode on the first gate insulating region opposite the integrated circuit substrate;

p-type spaced apart source and drain regions in the integrated circuit substrate;

a second gate insulating region on the integrated circuit substrate between the p-type spaced apart source and drain regions; and

a second gate electrode on the second gate insulating region opposite the integrated circuit substrate,

wherein the first gate electrode comprises an Ru-Ta alloy having at least about 30% Ta and wherein the second gate electrode comprises an Ru-Ta alloy having less than about 30% Ta.

14. (Currently Amended) An integrated circuit ~~electrode according to Claim 5~~ comprising:

spaced apart source and drain regions in an integrated circuit substrate;  
a first gate insulating region on the integrated circuit substrate between the  
spaced apart source and drain regions;  
a first gate electrode on the first gate insulating region opposite the integrated  
circuit substrate, wherein the first gate electrode comprises an alloy comprising a first  
metal and a second metal having lower work function than the first metal;  
a second gate insulating region on the integrated circuit substrate between the  
spaced apart source and drain regions; and  
a second gate electrode on the second gate insulating region opposite the  
integrated circuit substrate, wherein the second gate electrode comprises an alloy  
comprising a first metal and a second metal having lower work function than the first  
metal to provide a multiple gate integrated circuit field effect transistor.

15. (Currently Amended) An integrated circuit electrode according to  
Claim [[1]] 14 wherein the first metal has a work function of greater than about 4.5eV  
and wherein the second metal has a work function of less than about 4.5eV.

16. (Currently Amended) An integrated circuit electrode according to  
Claim [[1]] 14 wherein the first metal has a work function of about 5eV and wherein  
the second metal has a work function of about 4eV.

17. (Currently Amended) An integrated circuit electrode according to  
Claim [[1]] 14 wherein the first metal has a work function of between about 5eV and  
about 5.2eV and wherein the second metal has a work function of between about 4eV  
and about 4.1eV.

18. (Currently Amended) An integrated circuit electrode according to  
Claim [[1]] 14 wherein the first metal has a work function of between about 5eV and  
about 5.2eV and wherein the second metal has a work function of between about  
3.5eV and about 4.0eV.

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19-38. (Withdrawn)